Appl. No. 10/661,793   Attorney Docket No.: TS01-1037
Amdt. dated 12/19/2005   N1085-90149
Response to Office Action of 09/19/2005

Amendments to the Claims:

This listing of claims will replace all prior versions and listings of claims in the application:

1   1.-7.   (Cancelled)

1   8.   (Currently Amended) A system for creation of an opening of controllable format
2   through a layer of insulation material, comprising:

3   means for creating an opening through a layer of etch resist material provided
4   over the surface of a layer of insulating material having been deposited over the surface
5   of a substrate;

6   means, including a feedback mechanism, for ~~assuring that~~ obtaining a critical
7   dimension measurement of said opening created through said layer of etch resist
8   material and assuring that said critical dimension measurement is within design
9   specification;

10   means for creating an said opening through said layer of insulation material,
11   whereby a diameter of said layer of insulation material is dependent on a diameter of
12   said opening created through said layer of etch resist material; and

13   means, including a feedback mechanism, for assuring that said opening created
14   through said layer of insulation material is within design specification.

1   9.   (Original) The system of claim 8, said means for assuring that said opening
2   created through said layer of etch resist material is within design specification
3   comprising:

4   means for linking to a software supervisory function, thereby including data
5   transmission functions;

SD\80953.1

6 means for linking to a software function equally being linked to a software

7 supervisory function, thereby including data transmission functions;

8 means for data manipulating capabilities, thereby including manipulating

9 interdependent data;

10 means for interfacing with semiconductor equipment, thereby including

11 equipment functioning in a supporting role to said semiconductor equipment; and

12 means for creating instructions for said semiconductor equipment, thereby

13 including equipment functioning in a supporting role to said semiconductor equipment.

1 10. (Original) The system of claim 8, said means for assuring that said opening

2 created through said layer of insulation material is within design specification

3 comprising:

4 means for linking to a software supervisory function, thereby including data

5 transmission functions;

6 means for linking to a software function equally being linked to a software

7 supervisory function, thereby including data transmission functions;

8 means for data manipulating capabilities, thereby including manipulating

9 interdependent data;

10 means for interfacing with semiconductor equipment, thereby including

11 equipment functioning in a supporting role to said semiconductor equipment; and

12 means for creating instructions for said semiconductor equipment, thereby

13 including equipment functioning in a supporting role to said semiconductor equipment.

1   11.   (Original) The system of claim 8, further comprising means for creating an

2   opening having non-linear sidewalls through a layer of insulation material by applying a

3   high-polymer based etch to the surface of said layer of insulation material.

1   12.   (Previously Presented) A system for creation of an opening of controllable format

2   through a layer of insulation material, comprising:

3   means for software processing capabilities, said software processing capabilities

4   comprising;

5   (i)   first software processing capabilities being photoresist processing based;

6   and

7   (ii)   second software processing capabilities being insulating layer etch based;

8   means for providing a parameter having a first value of After Development

9   Inspection Critical Dimension (ADI CD) to said first software processing capability, said

10 ADI CD being a diameter of an opening being created through a layer of photoresist;

11   means for evaluating issuance of a first instruction, comprising;

12   (i)   a first instruction having been issued, modifying said first value of ADI CD

13 based on said first instruction, creating a second value of ADI CD; and

14   (ii)   no first instruction having been issued, converting said step of evaluation

15 for a first instruction having been issued into a no-op or void step;

16   means for coating a layer of photoresist over the surface of said layer of

17 insulation material;

18   means for developing said layer of photoresist, creating an opening having a

19 diameter of a second value of ADI CD through said layer of photoresist;

Page 4 of 15

20   means for measuring said second value of ADI CD;

21   means for determining a first difference between said second value of ADI CD
22   and said first value of ADI CD;

23   means for creating said first instruction based on said first difference, said first
24   instruction comprising:

25   (i)   continuing processing said substrate, said instruction of continue
26   processing said substrate being indicative of said first difference being less than a first
27   ADI CD inspection limit, said continue processing said substrate proceeding with a
28   subsequently specified step of step of providing a parameter having a value of said
29   second value ADI CD to said second software processing capability;

30   (ii)   removing said developed layer of photoresist from the surface of said
31   layer of insulation material, further invoke said step of modifying said first value of ADI
32   CD based on said first instruction, said first value of ADI CD of said modifying taking on
33   the value of said second value of ADI CD, followed by said steps specified herein
34   following said step of evaluating issuance of a first instruction, said instruction of invoke
35   said modifying said first value of ADI CD based on a first instruction being indicative of
36   said first difference being less than a first ADI CD inspection limit;

37   (iii)   discontinuing processing said substrate, said instruction of discontinue
38   processing said substrate being indicative of said first difference being more than a
39   second ADI CD inspection limit, said instruction of discontinue processing said
40   substrate further being indicative of a judgement that processing said wafer must be
41   discontinued;

42   means for executing said first instruction;

43   means for providing a parameter having a value of said second value ADI CD to
44   said second software processing capability;

SD\80953.1

Appl. No. 10/661,793   Attorney Docket No.: TS01-1037
Amdt. dated 12/19/2005   N1085-90149
Response to Office Action of 09/19/2005

45   means for first modifying said second value of ADI CD based on an equation,

46   creating a first value of After Etch Inspection Critical Dimension (AEI CD);

47   means for evaluating issuance of a second instruction, comprising:

48   (i)   a second instruction having been issued, modifying said first value of AEI

49   CD based on said second instruction, creating a second value of AEI CD; and

50   (ii)   no second instruction having been issued, converting said step of

51   evaluation for a second instruction having been issued into a no-op or void step;

52   means for etching an opening having a diameter of a second value of AEI CD

53   through said layer of insulation;

54   means for measuring said second value of AEI CD;

55   means for determining a second difference between said second value of AEI

56   CD and said first value of AEI CD;

57   means for determining said second instruction based on said second difference,

58   said second instructions comprising:

59   (i)   continuing processing said substrate, said instruction of continue

60   processing said substrate being indicative of said first difference being less than a first

61   AEI CD inspection limit, said continue processing said substrate resulting in termination

62   of said second software processing, thereby releasing said substrate for additional

63   processing not under control of said first and second software processing capabilities;

64   (ii)   invoking said second modifying said first value of AEI CD based on a

65   second instruction, said first value of said second modifying of AEI CD taking on the

66   value of said second value of AEI CD, followed by said steps specified herein following

67   said step of second modifying said first value of AEI CD based on a second instruction,

68   said instruction of invoke said modifying said first value of AEI CD based on first

SD\80953.1

69   instructions being indicative of said first difference being less than a first AEI CD

70   inspection limit;

71   (iii)   discontinuing processing said substrate, said instruction of discontinue

72   processing said substrate being indicative of said first difference being more than a

73   second ADI CD inspection limit; and

74   means for executing said second instruction.

1   13.   (Original) The system of claim 12, said first software processing capabilities

2   comprising:

3   means for linking to a supervisory software function;

4   means for accepting first data from and providing first data to said supervisory

5   software function, thereby including data of ADI CD and AEI CD;

6   means for calculating data, creating first output data, based on first input data

7   and in accordance with a first relationship as embodied in a first equation between said

8   first input data and said first output value for ADI CD based on a first input value of ADI

9   CD;

10   means for providing to and accepting from photoresist processing equipment

11   data that relate to photoresist processing, thereby including a value of ADI CD;

12   means for providing to and accepting from photoresist related processing

13   equipment instructions of or relating to performance of operations by said photoresist

14   related processing equipment, thereby including an instruction to measure a diameter of

15   an opening created through said layer of photoresist, thereby further including receiving

16   first measurement results of a first diameter of a first opening created through said layer

17   of photoresist;

SD\80953.1

Appl. No. 10/661,793   Attorney Docket No.: TS01-1037
Amdt. dated 12/19/2005   N1085-90149
Response to Office Action of 09/19/2005

18   means for calculating a first difference between numerical values, thereby
19   included calculating a first difference between a first value of ADI CD and a measured
20   value of ADI CD;

21   means for evaluating results obtained by said calculating a first difference
22   between numerical values; and

23   means for creating first instructions relating to said first software processing
24   capabilities being photoresist processing based, thereby including first instructions of
25   terminating photoresist processing, of continuing photoresist processing or of invoking
26   said function of calculating data, creating output data of said first software processing
27   capabilities.

1   14.   (Original) The system of claim 12, said second software processing capabilities
2   comprising:

3   means for linking to said first software processing capabilities;

4   means for accepting second data from and providing second data to said second
5   software processing capabilities, thereby including data of ADI CD and AEI CD;

6   means for calculating data, creating second output data, based on second input
7   data and in accordance with a second relationship as embodied in a second equation
8   between said second input data and said second output data, thereby including
9   calculating a first output value for AEI CD based on a first input value of ADI CD,
10   thereby further including calculating a second output value for AEI CD based on a
11   second input value for AEI CD;

12   means for providing to and accepting from etch processing equipment data that
13   relate to etch processing, thereby including a value of ADI CD, thereby further including
14   a value of AEI CD;

Page 8 of 15

15   means for providing to and accepting from etch related processing equipment
16   instructions of or relating to performance of operations by said etch related processing
17   equipment, thereby including an instruction to measure a diameter of an opening
18   created through said layer of insulation material, thereby further including receiving first
19   measurement results of a first diameter of a first opening created through said layer of
20   insulation material;

21   means for calculating a second difference between numerical values, thereby
22   included calculating a second difference between a first value of AEI CD and a
23   measured value of AEI CD;

24   means for evaluating results obtained by said calculating a second difference
25   between numerical values; and

26   means for creating second instructions relating to said second software
27   processing capabilities being etch processing based, thereby including second
28   instructions of terminating etch processing, of continuing etch processing or of invoking
29   said function of calculating data, creating output data of said second software
30   processing capabilities.

SD\80953.1